

# James H Edgar

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

262 papers	5,774 citations	37 h-index	68 g-index
281 ext. papers	6,922 ext. citations	6.5 avg, IF	5.9 L-index

#	Paper	IF	Citations
262	Phonon-Enhanced Mid-Infrared CO <sub>2</sub> Gas Sensing Using Boron Nitride Nanoresonators. <i>ACS Photonics</i> , <b>2022</b> , 9, 34-42	6.3	3
261	Bernal Boron Nitride Crystals Identified by Deep-Ultraviolet Cryomicroscopy.. <i>ACS Nano</i> , <b>2022</b> ,	16.7	1
260	Polytypes of sp <sup>2</sup> -Bonded Boron Nitride. <i>Crystals</i> , <b>2022</b> , 12, 782	2.3	1
259	Active and Passive Tuning of ultra-narrow Resonances in Polaritonic Nanoantennas.. <i>Advanced Materials</i> , <b>2021</b> , e2104954	24	1
258	Graphene's non-equilibrium fermions reveal Doppler-shifted magnetophonon resonances accompanied by Mach supersonic and Landau velocity effects. <i>Nature Communications</i> , <b>2021</b> , 12, 6392	17.4	0
257	Radiative lifetime of free excitons in hexagonal boron nitride. <i>Physical Review B</i> , <b>2021</b> , 104,	3.3	1
256	Polaritonic Vortices with a Half-Integer Charge. <i>Nano Letters</i> , <b>2021</b> , 21, 9256-9261	11.5	3
255	Ellipsometry Study of Hexagonal Boron Nitride Using Synchrotron Radiation: Transparency Window in the Far-UVC. <i>Advanced Photonics Research</i> , <b>2021</b> , 2, 2000101	1.9	5
254	Hybrid Waveguides: Guided Mid-IR and Near-IR Light within a Hybrid Hyperbolic-Material/Silicon Waveguide Heterostructure (Adv. Mater. 11/2021). <i>Advanced Materials</i> , <b>2021</b> , 33, 2170079	24	
253	Band structure and ultraviolet optical transitions in ErN. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 131108	3.4	2
252	Direct Laser Patterning of a 2D WSe <sub>2</sub> Logic Circuit. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2009549	15.6	6
251	Hexagonal Boron Nitride Crystal Growth from Iron, a Single Component Flux. <i>ACS Nano</i> , <b>2021</b> , 15, 7032-7039	16.7	11
250	Programmable Bloch polaritons in graphene. <i>Science Advances</i> , <b>2021</b> , 7,	14.3	1
249	Spatiotemporal imaging of 2D polariton wave packet dynamics using free electrons. <i>Science</i> , <b>2021</b> , 372, 1181-1186	33.3	8
248	Isotope effect on the thermal expansion coefficient of atomically thin boron nitride. <i>2D Materials</i> , <b>2021</b> , 8, 034006	5.9	1
247	Determination of the optical bandgap of the Bernal and rhombohedral boron nitride polymorphs. <i>Physical Review Materials</i> , <b>2021</b> , 5,	3.2	6
246	Fizeau drag in graphene plasmonics. <i>Nature</i> , <b>2021</b> , 594, 513-516	50.4	20

245	Long-Lived Phonon Polaritons in Hyperbolic Materials. <i>Nano Letters</i> , <b>2021</b> , 21, 5767-5773	11.5	11
244	Planar refraction and lensing of highly confined polaritons in anisotropic media. <i>Nature Communications</i> , <b>2021</b> , 12, 4325	17.4	12
243	Real-space observation of vibrational strong coupling between propagating phonon polaritons and organic molecules. <i>Nature Photonics</i> , <b>2021</b> , 15, 197-202	33.9	26
242	Irradiation Response on the Electronic Transport Properties of p-B12P2. <i>Journal of Electronic Materials</i> , <b>2021</b> , 50, 75-79	1.9	
241	Enhanced Light-Matter Interaction in 10B Monoisotopic Boron Nitride Infrared Nanoresonators. <i>Advanced Optical Materials</i> , <b>2021</b> , 9, 2001958	8.1	11
240	Total Internal Reflection Peak Force Infrared Microscopy. <i>Analytical Chemistry</i> , <b>2021</b> , 93, 731-736	7.8	4
239	Hall Effect Characterization of Irradiated p-Type 4H-SiC. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 1900781	1.3	
238	Amplitude- and Phase-Resolved Infrared Nanoimaging and Nanospectroscopy of Polaritons in a Liquid Environment. <i>Nano Letters</i> , <b>2021</b> , 21, 1360-1367	11.5	3
237	Van der Waals engineering of ferroelectric heterostructures for long-retention memory. <i>Nature Communications</i> , <b>2021</b> , 12, 1109	17.4	29
236	Guided Mid-IR and Near-IR Light within a Hybrid Hyperbolic-Material/Silicon Waveguide Heterostructure. <i>Advanced Materials</i> , <b>2021</b> , 33, e2004305	24	7
235	Phonons of hexagonal BN under pressure: Effects of isotopic composition. <i>Physical Review B</i> , <b>2021</b> , 103,	3.3	1
234	Revealing Nanoscale Confinement Effects on Hyperbolic Phonon Polaritons with an Electron Beam. <i>Small</i> , <b>2021</b> , 17, e2103404	11	6
233	Ultrahigh-Resolution, Label-Free Hyperlens Imaging in the Mid-IR. <i>Nano Letters</i> , <b>2021</b> , 21, 7921-7928	11.5	8
232	Experimental confirmation of long hyperbolic polariton lifetimes in monoisotopic (10B) hexagonal boron nitride at room temperature. <i>APL Materials</i> , <b>2021</b> , 9, 091109	5.7	1
231	Flat Bands and Giant Light-Matter Interaction in Hexagonal Boron Nitride. <i>Physical Review Letters</i> , <b>2021</b> , 127, 137401	7.4	5
230	Rhombohedral and turbostratic boron nitride: X-ray diffraction and photoluminescence signatures. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 262102	3.4	2
229	Hexagonal Boron Nitride Single Crystal Growth from Solution with a Temperature Gradient. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 5066-5072	9.6	8
228	Manipulating phonon polaritons in low loss B enriched hexagonal boron nitride with polarization control. <i>Nanoscale</i> , <b>2020</b> , 12, 8188-8193	7.7	3

227	Peakforce Infrared Microscopy: Revealing Phonon Polaritons in Hexagonal Boron Nitride by Multipulse Peak Force Infrared Microscopy (Advanced Optical Materials 5/2020). <i>Advanced Optical Materials</i> , <b>2020</b> , 8, 2070021	8.1	
226	Single crystal growth of monoisotopic hexagonal boron nitride from a Fe <sub>2</sub> Ir flux. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 9931-9935	7.1	6
225	Nanoscale Guiding of Infrared Light with Hyperbolic Volume and Surface Polaritons in van der Waals Material Ribbons. <i>Advanced Materials</i> , <b>2020</b> , 32, e1906530	24	17
224	Band structure and infrared optical transitions in ErN. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 171104	3.4	4
223	Properties of bulk scandium nitride crystals grown by physical vapor transport. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 132103	3.4	6
222	Isotopic Disorder: The Prevailing Mechanism in Limiting the Phonon Lifetime in Hexagonal BN. <i>Physical Review Letters</i> , <b>2020</b> , 124, 167402	7.4	9
221	Probing Mid-Infrared Phonon Polaritons in the Aqueous Phase. <i>Nano Letters</i> , <b>2020</b> , 20, 3986-3991	11.5	10
220	High Q-factor resonators and nanoantennas based on phonon polaritons in van der Waals materials <b>2020</b> ,		1
219	Revealing Phonon Polaritons in Hexagonal Boron Nitride by Multipulse Peak Force Infrared Microscopy. <i>Advanced Optical Materials</i> , <b>2020</b> , 8, 1901084	8.1	9
218	Three-dimensional near-field analysis through peak force scattering-type near-field optical microscopy. <i>Nanoscale</i> , <b>2020</b> , 12, 1817-1825	7.7	5
217	Image polaritons in boron nitride for extreme polariton confinement with low losses. <i>Nature Communications</i> , <b>2020</b> , 11, 3649	17.4	21
216	Isotopically Enhanced Thermal Conductivity in Few-Layer Hexagonal Boron Nitride: Implications for Thermal Management. <i>ACS Applied Nano Materials</i> , <b>2020</b> , 3, 12148-12156	5.6	4
215	Cathodoluminescence and x-ray photoelectron spectroscopy of ScN: Dopant, defects, and band structure. <i>APL Materials</i> , <b>2020</b> , 8, 081103	5.7	6
214	Collective near-field coupling and nonlocal phenomena in infrared-phononic metasurfaces for nano-light canalization. <i>Nature Communications</i> , <b>2020</b> , 11, 3663	17.4	35
213	Pressure dependence of the interlayer and intralayer E2g Raman-active modes of hexagonal BN up to the wurtzite phase transition. <i>Physical Review B</i> , <b>2020</b> , 102,	3.3	5
212	Structural and electronic transitions in few layers of isotopically pure hexagonal boron nitride. <i>Physical Review B</i> , <b>2020</b> , 102,	3.3	2
211	Outstanding Thermal Conductivity of Single Atomic Layer Isotope-Modified Boron Nitride. <i>Physical Review Letters</i> , <b>2020</b> , 125, 085902	7.4	21
210	Deep ultraviolet hyperspectral cryomicroscopy in boron nitride: Photoluminescence in crystals with an ultra-low defect density. <i>AIP Advances</i> , <b>2020</b> , 10, 075025	1.5	10

209	Excellent electronic transport in heterostructures of graphene and monoisotopic boron-nitride grown at atmospheric pressure. <i>2D Materials</i> , <b>2020</b> , 7, 031009	5.9	11
208	Giant oscillations in a triangular network of one-dimensional states in marginally twisted graphene. <i>Nature Communications</i> , <b>2019</b> , 10, 4008	17.4	36
207	Polariton nanophotonics using phase-change materials. <i>Nature Communications</i> , <b>2019</b> , 10, 4487	17.4	53
206	Rapid Bimolecular and Defect-Assisted Carrier Recombination in Hexagonal Boron Nitride. <i>Journal of Physical Chemistry C</i> , <b>2019</b> , 123, 14689-14695	3.8	1
205	Modulating the thermal conductivity in hexagonal boron nitride via controlled boron isotope concentration. <i>Communications Physics</i> , <b>2019</b> , 2,	5.4	67
204	Predicting the preferred morphology of hexagonal boron nitride domain structure on nickel from ReaxFF-based molecular dynamics simulations. <i>Nanoscale</i> , <b>2019</b> , 11, 5607-5616	7.7	12
203	Influence of isotopic substitution on the anharmonicity of the interlayer shear mode of h-BN. <i>Physical Review B</i> , <b>2019</b> , 99,	3.3	9
202	Photonics with hexagonal boron nitride. <i>Nature Reviews Materials</i> , <b>2019</b> , 4, 552-567	73.3	253
201	Strong magnetophonon oscillations in extra-large graphene. <i>Nature Communications</i> , <b>2019</b> , 10, 3334	17.4	14
200	Refractive Index-Based Control of Hyperbolic Phonon-Polariton Propagation. <i>Nano Letters</i> , <b>2019</b> , 19, 7725-7734	11.5	39
199	Photonic crystal for graphene plasmons. <i>Nature Communications</i> , <b>2019</b> , 10, 4780	17.4	30
198	Shallow and deep levels in carbon-doped hexagonal boron nitride crystals. <i>Physical Review Materials</i> , <b>2019</b> , 3,	3.2	22
197	A cooling fin to enhance the efficiency of crystal growth by physical vapor transport. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2019</b> , 251, 114443	3.1	1
196	Micromagnetometry of two-dimensional ferromagnets. <i>Nature Electronics</i> , <b>2019</b> , 2, 457-463	28.4	46
195	Hexagonal Boron Nitride Single Crystal Thermal Oxidation and Etching in Air: An Atomic Force Microscopy Study. <i>MRS Advances</i> , <b>2019</b> , 4, 601-608	0.7	2
194	Infrared hyperbolic metasurface based on nanostructured van der Waals materials. <i>Science</i> , <b>2018</b> , 359, 892-896	33.3	215
193	Isotopic effects on phonon anharmonicity in layered van der Waals crystals: Isotopically pure hexagonal boron nitride. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	34
192	Single photon emission from plasma treated 2D hexagonal boron nitride. <i>Nanoscale</i> , <b>2018</b> , 10, 7957-7965	7.7	64

191	Effects of High-Energy Electron Irradiation on Quantum Emitters in Hexagonal Boron Nitride. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 24886-24891	9.5	38
190	Sublimation Growth and Characterization of Erbium Nitride Crystals. <i>Crystal Growth and Design</i> , <b>2018</b> , 18, 3762-3766	3.5	9
189	Cubic boron phosphide epitaxy on zirconium diboride. <i>Journal of Crystal Growth</i> , <b>2018</b> , 483, 115-120	1.6	7
188	Ultralow-loss polaritons in isotopically pure boron nitride. <i>Nature Materials</i> , <b>2018</b> , 17, 134-139	27	191
187	Isotope engineering of van der Waals interactions in hexagonal boron nitride. <i>Nature Materials</i> , <b>2018</b> , 17, 152-158	27	66
186	Suppression of Rotational Twins in Epitaxial B12P2 on 4H-SiC. <i>Crystal Growth and Design</i> , <b>2018</b> , 18, 669-676	3.6	2
185	Probing hyperbolic polaritons using infrared attenuated total reflectance micro-spectroscopy. <i>MRS Communications</i> , <b>2018</b> , 8, 1418-1425	2.7	12
184	Bulk (100) scandium nitride crystal growth by sublimation on tungsten single crystal seeds. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 122106	3.4	7
183	Reconfigurable infrared hyperbolic metasurfaces using phase change materials. <i>Nature Communications</i> , <b>2018</b> , 9, 4371	17.4	92
182	Single Crystal Growth of Millimeter-Sized Monoisotopic Hexagonal Boron Nitride. <i>Chemistry of Materials</i> , <b>2018</b> , 30, 6222-6225	9.6	63
181	Elements of Structures and Defects of Crystalline Materials by Tsang-Tse Fang. <i>MRS Bulletin</i> , <b>2018</b> , 43, 981-982	3.2	
180	Determining crystal phase purity in c-BP through X-ray absorption spectroscopy. <i>Physical Chemistry Chemical Physics</i> , <b>2017</b> , 19, 8174-8187	3.6	7
179	Detection of defect populations in superhard semiconductor boron subphosphide B12P2 through X-ray absorption spectroscopy. <i>Journal of Materials Chemistry A</i> , <b>2017</b> , 5, 5737-5749	13	6
178	Hydride CVD Hetero-epitaxy of B12P2 on 4H-SiC. <i>Journal of Crystal Growth</i> , <b>2017</b> , 459, 112-117	1.6	4
177	Phonon states of B12P2 crystals: Ab initio calculation and experiment. <i>Journal of Physics and Chemistry of Solids</i> , <b>2017</b> , 110, 248-253	3.9	4
176	MoS2/h-BN heterostructures: controlling MoS2 crystal morphology by chemical vapor deposition. <i>Journal of Materials Science</i> , <b>2017</b> , 52, 7028-7038	4.3	9
175	Atomistic Insights into Nucleation and Formation of Hexagonal Boron Nitride on Nickel from First-Principles-Based Reactive Molecular Dynamics Simulations. <i>ACS Nano</i> , <b>2017</b> , 11, 3585-3596	16.7	37
174	Large-Scale Growth of High-Quality Hexagonal Boron Nitride Crystals at Atmospheric Pressure from an FeCl <sub>3</sub> Flux. <i>Crystal Growth and Design</i> , <b>2017</b> , 17, 4932-4935	3.5	29

173	Assessing Hexagonal Boron Nitride Crystal Quality by Defect Sensitive Etching. <i>Microscopy and Microanalysis</i> , <b>2017</b> , 23, 1518-1519	0.5	
172	Exciton-phonon interaction in the strong-coupling regime in hexagonal boron nitride. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	23
171	The high-pressure compressibility of B12P2. <i>Journal of Physics and Chemistry of Solids</i> , <b>2017</b> , 102, 21-26	3.9	9
170	Defect sensitive etching of hexagonal boron nitride single crystals. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 225110	2.5	8
169	Distinctive in-Plane Cleavage Behaviors of Two-Dimensional Layered Materials. <i>ACS Nano</i> , <b>2016</b> , 10, 8980-8987	4.7	60
168	Self-healing in B12P2 through Mediated Defect Recombination. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 8415-8428	4.8	7
167	CVD growth and properties of boron phosphide on 3C-SiC. <i>Journal of Crystal Growth</i> , <b>2016</b> , 449, 15-21	1.6	8
166	Epitaxy of Boron Phosphide on Aluminum Nitride(0001)/Sapphire Substrate. <i>Crystal Growth and Design</i> , <b>2016</b> , 16, 981-987	3.5	45
165	Exploiting the P L <sub>2,3</sub> absorption edge for optics: spectroscopic and structural characterization of cubic boron phosphide thin films. <i>Optical Materials Express</i> , <b>2016</b> , 6, 3946	2.6	8
164	Photocurrent response of B12As2 crystals to blue light, and its temperature- dependent electrical characterizations. <i>AIP Advances</i> , <b>2016</b> , 6, 025206	1.5	1
163	Nature of exciton transitions in hexagonal boron nitride. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 122101	3.4	14
162	Perfect interferenceless absorption at infrared frequencies by a van der Waals crystal. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	32
161	Effect of GaN surface treatment on Al <sub>2</sub> O <sub>3</sub> /n-GaN MOS capacitors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 061201	1.3	22
160	Sintered Cr/Pt and Ni/Au ohmic contacts to B12P2. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2015</b> , 33, 031101	2.9	2
159	Preparation, properties, and characterization of boron phosphide films on 4H- and 6H-silicon carbide. <i>Solid State Sciences</i> , <b>2015</b> , 47, 55-60	3.4	17
158	Temperature dependence of the energy bandgap of two-dimensional hexagonal boron nitride probed by excitonic photoluminescence. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 053503	2.5	14
157	Atomic layer deposition TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> stack: An improved gate dielectric on Ga-polar GaN metal oxide semiconductor capacitors. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 060602	1.3	3
156	Comparison of the physical, chemical and electrical properties of ALD Al <sub>2</sub> O <sub>3</sub> on c- and m- plane GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 898-901		4



155	Equation of state of single-crystal cubic boron phosphide. <i>Journal of Superhard Materials</i> , <b>2014</b> , 36, 61-64.	0.9	8
154	Optimization of Ni-Fe flux growth for hexagonal boron nitride single crystals. <i>Journal of Crystal Growth</i> , <b>2014</b> , 393, 114-118	1.6	42
153	Characterization of bulk hexagonal boron nitride single crystals grown by the metal flux technique. <i>Journal of Crystal Growth</i> , <b>2014</b> , 403, 110-113	1.6	24
152	Insulating gallium oxide layer produced by thermal oxidation of gallium-polar GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 565-568		11
151	A Comparison of N-Polar (0001) GaN Surface Preparations for the Atomic Layer Deposition of Al <sub>2</sub> O <sub>3</sub> . <i>ECS Journal of Solid State Science and Technology</i> , <b>2014</b> , 3, N127-N131	2	11
150	Growth of hBN Using Metallic Boron: Isotopically Enriched h <sup>10</sup> BN and h <sup>11</sup> BN. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1635, 35-40		2
149	The coefficients of thermal expansion of boron arsenide (B <sub>12</sub> As <sub>2</sub> ) between 25°C and 850°C. <i>Journal of Physics and Chemistry of Solids</i> , <b>2013</b> , 74, 673-676	3.9	6
148	Influence of Atomic Layer Deposition Temperatures on TiO <sub>2</sub> /n-Si MOS Capacitor. <i>ECS Journal of Solid State Science and Technology</i> , <b>2013</b> , 2, N110-N114	2	34
147	Two-dimensional excitons in three-dimensional hexagonal boron nitride. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 191106	3.4	63
146	Seebeck Coefficient and Electrical Resistivity of Single Crystal B <sub>12</sub> As <sub>2</sub> at High Temperatures. <i>Journal of the Physical Society of Japan</i> , <b>2013</b> , 82, 095001	1.5	8
145	Polarity determination of rough and smooth surface grains in AlN crystals. <i>Crystal Research and Technology</i> , <b>2012</b> , 47, 1134-1139	1.3	1
144	Growth mechanisms and defect structures of B <sub>12</sub> As <sub>2</sub> epilayers grown on 4 H-SiC substrates. <i>Journal of Crystal Growth</i> , <b>2012</b> , 352, 3-8	1.6	5
143	Synthesis of Icosahedral Boron Arsenide Nanowires for Betavoltaic Applications. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1439, 69-75		1
142	Photoluminescence investigation of the indirect band gap and shallow impurities in icosahedral B <sub>12</sub> As <sub>2</sub> . <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 013508	2.5	12
141	High pressure X-ray diffraction study on icosahedral boron arsenide (B <sub>12</sub> As <sub>2</sub> ). <i>Journal of Physics and Chemistry of Solids</i> , <b>2011</b> , 72, 144-146	3.9	14
140	Semiconducting icosahedral boron arsenide crystal growth for neutron detection. <i>Journal of Crystal Growth</i> , <b>2011</b> , 318, 553-557	1.6	11
139	Solution Growth and Characterization of Icosahedral Boron Arsenide (B <sub>12</sub> As <sub>2</sub> ). <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1307, 1		
138	Elimination of Degenerate Epitaxy in the Growth of High Quality B <sub>12</sub> As <sub>2</sub> Single Crystalline Epitaxial Films. <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1307, 1		3



137	Electrical Characteristics of GaN and Si Based Metal-Oxide-Semiconductor (MOS) Capacitors. <i>ECS Transactions</i> , <b>2011</b> , 41, 429-437	1	2
136	Defect-Selective Etching of Icosahedral Boron Arsenide (B12As2) Crystals in Molten Potassium Hydroxide. <i>Materials Research Society Symposia Proceedings</i> , <b>2011</b> , 1307, 1		
135	Demonstration of boron arsenide heterojunctions: A radiation hard wide band gap semiconductor device. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 223506	3.4	13
134	Thermal conductivity and Seebeck coefficients of icosahedral boron arsenide films on silicon carbide. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 084906	2.5	10
133	Mechanism for Improved Quality B12As2 Epitaxial Films on (0001) 4H-SiC Substrates Offcut towards [1100]. <i>Materials Research Society Symposia Proceedings</i> , <b>2010</b> , 1246, 1		4
132	Electronic excitations in B12As2 and their temperature dependence by vacuum ultraviolet ellipsometry. <i>Journal of Physics Condensed Matter</i> , <b>2010</b> , 22, 395801	1.8	3
131	Photopolymerization of self-assembled monolayers of diacetylenic alkylphosphonic acids on group-III nitride substrates. <i>Langmuir</i> , <b>2010</b> , 26, 10725-30	4	17
130	Energy band structure and optical response function of icosahedral B12As2: A spectroscopic ellipsometry and first-principles calculational study. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	19
129	Nucleation Mechanism of 6H-SiC Polytype Inclusions Inside 15R-SiC Crystals. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 799-804	1.9	3
128	Sublimation growth of titanium nitride crystals. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2010</b> , 21, 78	2.1	9
127	Sublimation crystal growth of yttrium nitride. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 2896-2903	1.6	13
126	Transmission electron microscopy study of defects in AlN crystals with rough and smooth surface grains. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 3479-3484	1.6	4
125	The origin of 2.78 eV emission and yellow coloration in bulk AlN substrates. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 262104	3.4	38
124	Attempt to Grow Rhombohedral Boron Crystals in Copper Solvent. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1164, 1		
123	Thermodynamic Analysis and Purification for Source Materials in Sublimation Crystal Growth of Aluminum Nitride. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1202, 77		2
122	Origins of Twinned Microstructures in B12As2 Epilayers Grown on (0001) 6H-SiC and Their Influence on Physical Properties. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1164, 1		
121	Growth of Boron Carbide Crystals from a Copper Flux. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1164, 1		
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